

isc Silicon PNP Power Transistors

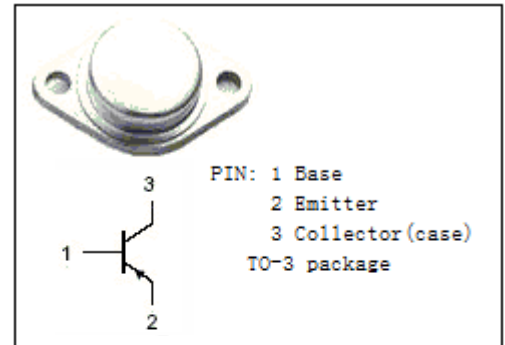
2N6379

DESCRIPTION

- Low Collector Saturation Voltage
- High DC Current Gain
- High Power Dissipation

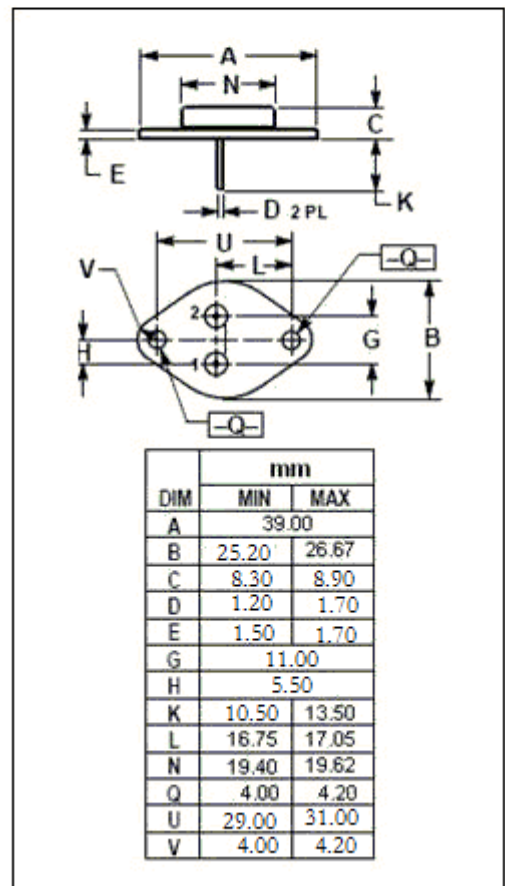
APPLICATIONS

- Designed for use in industrial-military power amplifier and switching circuit application.



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-140	V
V _{CE0}	Collector-Emitter Voltage	-120	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current-Continuous	-50	A
I _B	Base Current-Continuous	-20	A
P _C	Collector Power Dissipation	250	W
T _J	Junction Temperature	-65~200	°C
T _{stg}	Storage Temperature	-65~200	°C



isc Silicon PNP Power Transistors**2N6379****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)1} ★	Collector-Emitter Saturation Voltage	I _C = -20A; I _B = -2A			-1.2	V
V _{CE(sat)2} ★	Collector-Emitter Saturation Voltage	I _C = -50A; I _B = -10A			-3.0	V
V _{BE(sat)1} ★	Base-Emitter Saturation Voltage	I _C = -20A; I _B = -2A			-1.8	V
V _{BE(sat)1} ★	Base-Emitter Saturation Voltage	I _C = -50A; I _B = -10A			-3.5	V
I _{EBO}	Collector Cutoff Current	V _{EB} = -6V; I _E = 0			-0.1	mA
h _{FE1} ★	DC Current Gain	I _C = -1A; V _{CE} = -4V	50			
h _{FE2} ★	DC Current Gain	I _C = -20A; V _{CE} = -4V	30		120	
h _{FE3} ★	DC Current Gain	I _C = -50A; V _{CE} = -4V	10			

★:Pulse Test:Pulse Width=300us,Duty Cycle=2.0%